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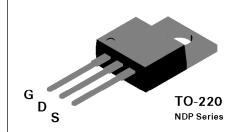
#### NDP6060L / NDB6060L N-Channel Logic Level Enhancement Mode Field Effect Transistor

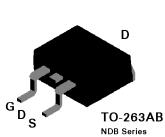
#### **General Description**

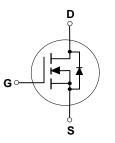
These logic level N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as automotive, DC/DC converters, PWM motor controls, and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

#### Features

- 48A, 60V.  $R_{DS(ON)} = 0.025\Omega @ V_{GS} = 5V.$
- Low drive requirements allowing operation directly from logic drivers. V<sub>GS(TH)</sub> < 2.0V.</li>
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- 175°C maximum junction temperature rating.
- High density cell design for extremely low R<sub>DS(ON)</sub>.
- TO-220 and TO-263 (D<sup>2</sup>PAK) package for both through hole and surface mount applications.







#### **Absolute Maximum Ratings** T<sub>c</sub> = 25°C unless otherwise noted

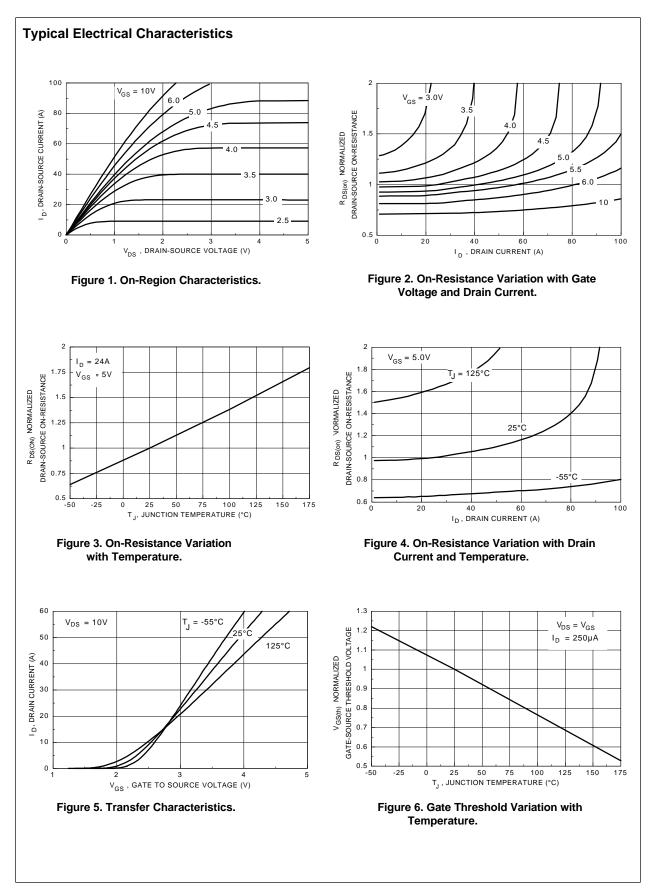
Symbol	Parameter	NDP6060L	NDB6060L	Units
V <sub>DSS</sub>	Drain-Source Voltage	60		V
V <sub>dgr</sub>	Drain-Gate Voltage ( $R_{GS} \leq 1 M\Omega$ )	60		V
$V_{GSS}$	Gate-Source Voltage - Continuous	± 16		V
	- Nonrepetitive ( $t_P < 50 \ \mu s$ )	±25		
I <sub>D</sub>	Drain Current - Continuous	48		А
	- Pulsed	144		
P <sub>D</sub>	Total Power Dissipation @ $T_c = 25^{\circ}C$	100		W
	Derate above 25°C	0.67		W/°C
Γ <sub>J</sub> ,T <sub>stg</sub>	Operating and Storage Temperature	-65 to 17	°C	
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	275		°C

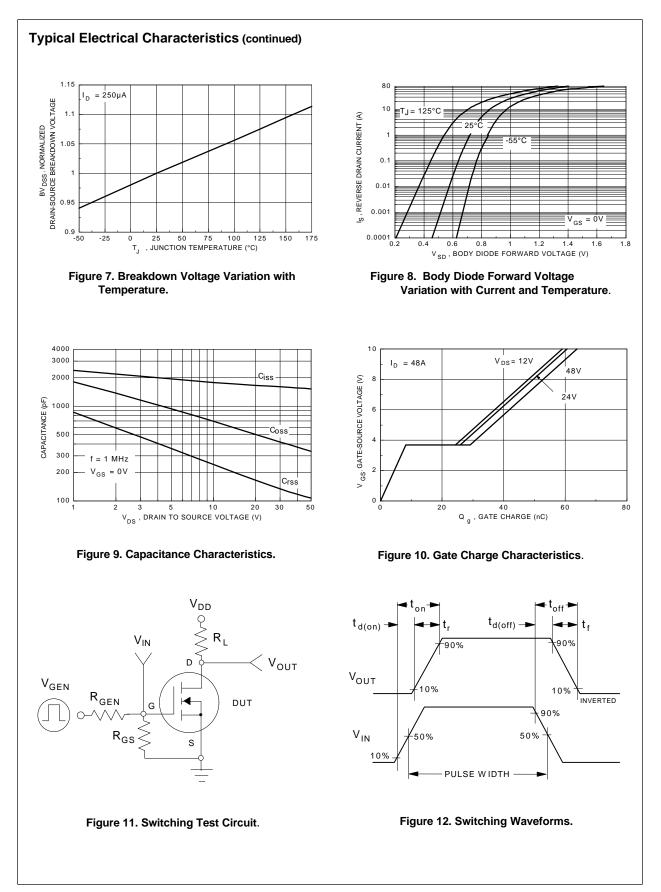
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Symbol	Parameter	Conditions		Min	Тур	Max	Units
DRAIN-S	OURCE AVALANCHE RATINGS (Note 1)						
W <sub>DSS</sub>	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 25 \text{ V}, \text{ I}_{D} = 48 \text{ A}$				200	mJ
I <sub>AR</sub>	Maximum Drain-Source Avalanche Cu	rrent				48	А
OFF CH/	ARACTERISTICS						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$		60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$				250	μA
			T <sub>J</sub> = 125°C			1	mA
I <sub>GSSF</sub>	Gate - Body Leakage, Forward	$V_{GS} = 16 \text{ V}, V_{DS} = 0 \text{ V}$				100	nA
I <sub>GSSR</sub>	Gate - Body Leakage, Reverse	$V_{GS} = -16 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$				-100	nA
ON CHAP	RACTERISTICS (Note 1)			•			
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$		1		2	V
			T <sub>J</sub> = 125°C	0.65		1.5	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = 5 \text{ V}, \text{ I}_{D} = 24 \text{ A}$				0.025	Ω
			T <sub>J</sub> = 125°C			0.04	
		$V_{GS} = 10 \text{ V}, I_{D} = 24 \text{ A}$				0.02	
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = 5 \text{ V}, V_{DS} = 10 \text{ V}$		48			А
9 <sub>FS</sub>	Forward Transconductance	$V_{\rm DS} = 10 \text{ V}, I_{\rm D} = 24 \text{ A}$		10			S
DYNAMI	CCHARACTERISTICS						
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz			1630	2000	pF
C <sub>oss</sub>	Output Capacitance				460	800	pF
C <sub>rss</sub>	Reverse Transfer Capacitance				150	400	рF
	NG CHARACTERISTICS (Note 1)				1		
t <sub>D(on)</sub>	Turn - On Delay Time	$V_{DD} = 30 \text{ V}, I_{D} = 48 \text{ A},$			15	30	nS
t,	Turn - On Rise Time	$V_{GS} = 5 \text{ V}, \text{R}_{GEN} = 15 \Omega,$ $\text{R}_{GS} = 15 \Omega$			320	500	nS
t <sub>D(off)</sub>	Turn - Off Delay Time				49	100	nS
t <sub>f</sub>	Turn - Off Fall Time				161	300	nS
 Q_	Total Gate Charge	$V_{DS} = 48 \text{ V},$ $I_{D} = 48 \text{ A}, V_{GS} = 5 \text{ V}$			36	60	nC
Q <sub>gs</sub>	Gate-Source Charge				8.2		nC
Q <sub>gd</sub>	Gate-Drain Charge	1			21		nC

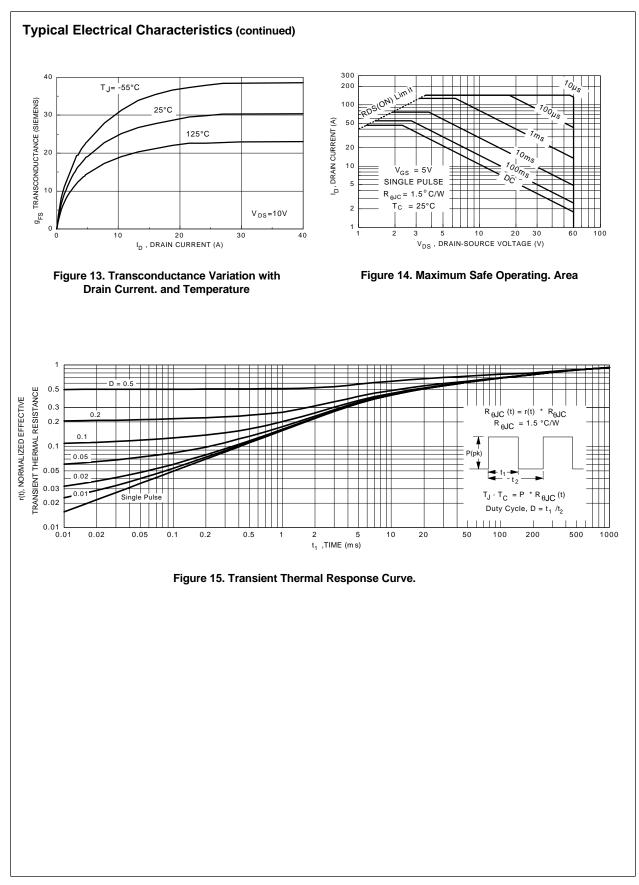
Electric	cal Characteristics (T <sub>c</sub> = 25°C unle	ess otherwise noted)					
Symbol	Parameter	Conditions		Min	Тур	Max	Units
DRAIN-SC	OURCE DIODE CHARACTERISTICS						
l <sub>s</sub>	Maximum Continuos Drain-Source Diode Forward Current				48	А	
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Fo	orward Current				144	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{S} = 24 \text{ A}$ (Note 1)				1.3	V
			T <sub>J</sub> = 125°C			1.2	
t <sub>m</sub>	Reverse Recovery Time	$V_{GS} = 0 V, I_F = 48 A,$		35	75	140	ns
l <sub>rr</sub>	Reverse Recovery Current	─ dl <sub>F</sub> /dt = 100 A/µs		2	3.6	8	A
THERMA	L CHARACTERISTICS					•	
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case					1.5	°C/W
R <sub>ØJA</sub>	Thermal Resistance, Junction-to-Ambient				62.5	°C/W	

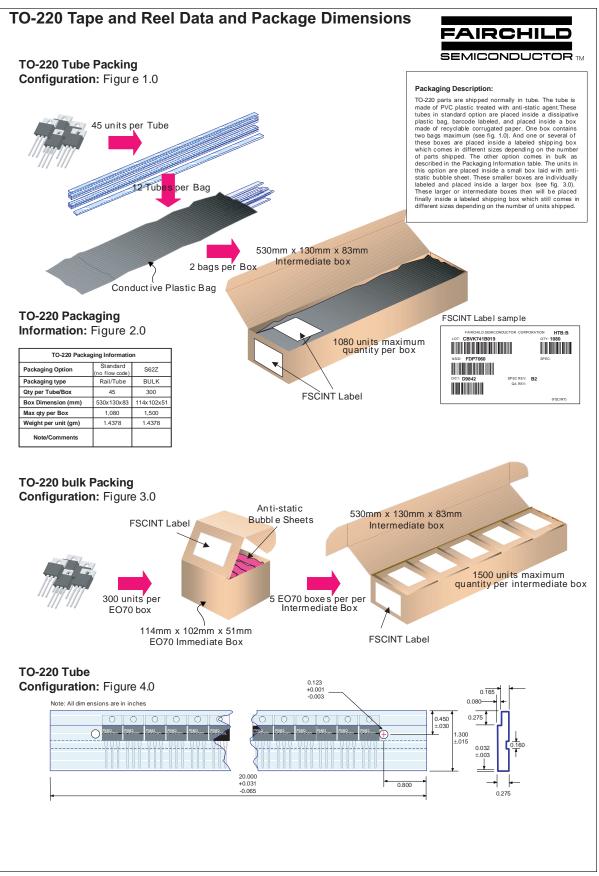
Note: 1. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.



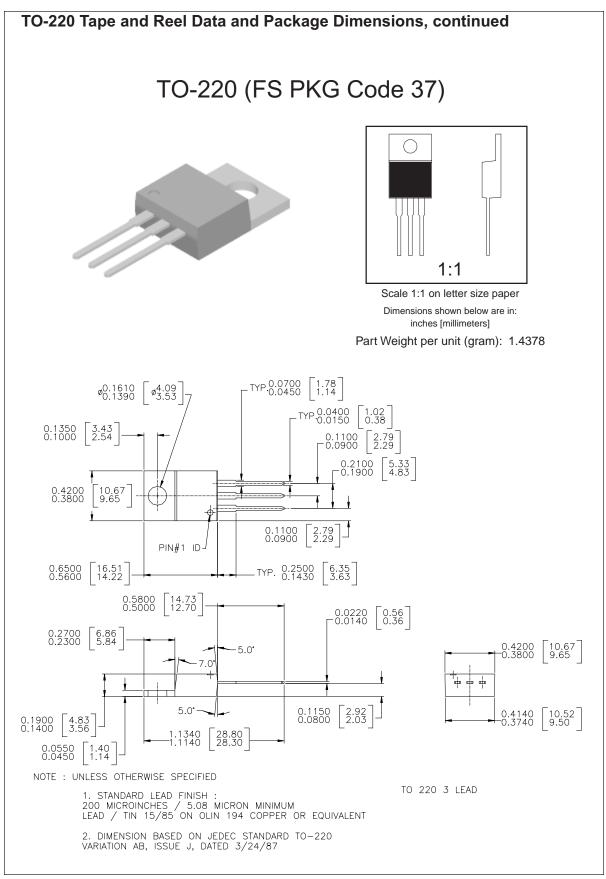


NDP6060L Rev. D / NDB6060L Rev. E

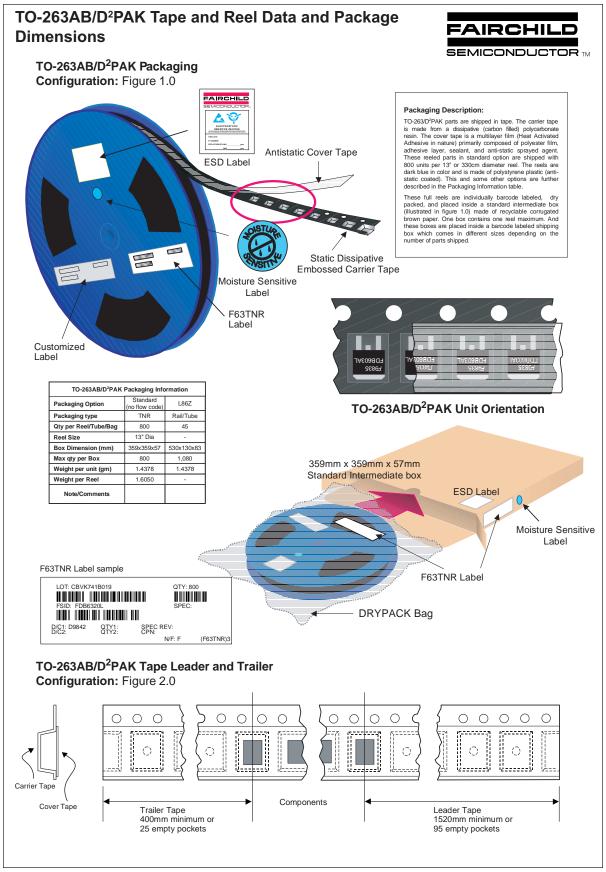




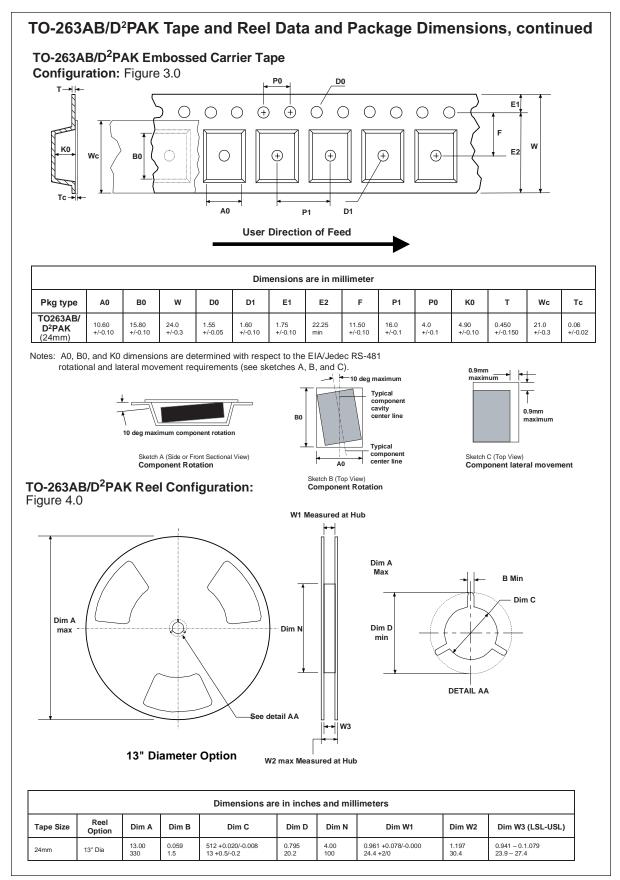
August 1999, Rev. B

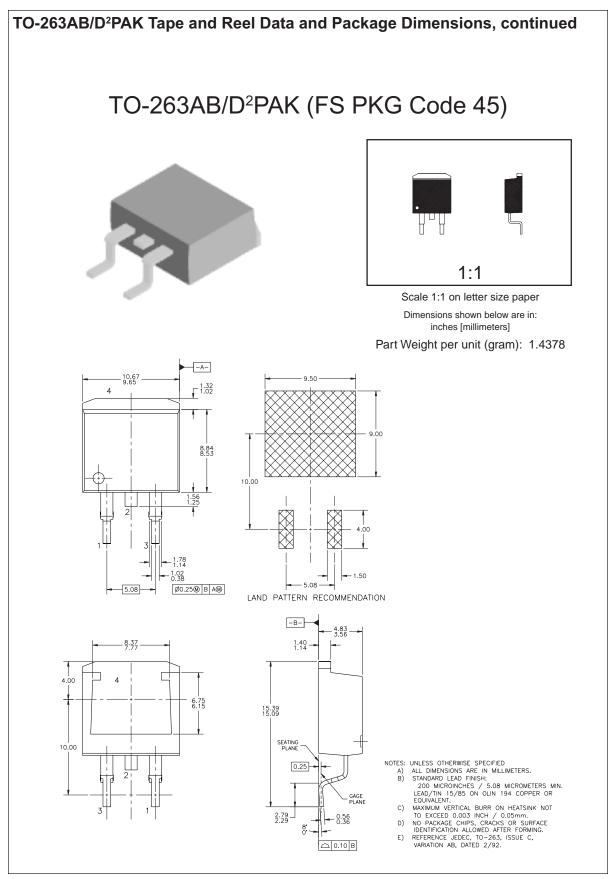


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